

EV549570797



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No. 10/615,051
Filing Date July 7, 2003
Inventorship Brian A. Vaartstra
Assignee Micron Technology, Inc.
Group Art Unit 2823
Examiner Brook Kebede
Attorney's Docket No. MI22-2308
Customer No. 021567
Title: Methods of Forming a Phosphorus Doped Silicon Dioxide-Comprising Layer

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - See Attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. Pursuant to FEDERAL REGISTER, Vol. 69, No. 182, pg. 56542 (September 21, 2004), no copies of any cited U.S. patents or U.S. published applications are included herewith. Copies of all other cited art are attached. No admission is made regarding whether all the submitted references are prior art.

This Supplemental Information Disclosure Statement is being filed before the mailing of a first office action after the filing of a Request for Continued Examination. Therefore, no fee is believed to be required. However, in the event that a fee is required for filing this Supplemental Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 5-4-05

By: 
Mark S. Matkin, Reg. No. 32,268

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTORNEY DOCKET NO. MI22-2308	SERIAL NO. 10/615,051
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT: Brian A. Vaartstra	
		FILING DATE 7/7/2003	GROUP ART UNIT 2823

*O I P E
MAY 04 2005
SEARCHED*

U.S. PATENT DOCUMENTS							
*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	6,013,583	1/11/2000	Ajmera et al.			
	AB	2001/0041250 A1	11/2001	Haukka et al.			
	AC	2002/0000195 A1	1/2002	Kao et al.			
	AD	2003/00129826 A1	7/10/2003	Werkhoven et al.			
	AE	2003/0032281 A1	2/13/2003	Werkhoven et al.			
	AF	5,770,469	6/1998	Uram et al.			
	AG	2004/0266153 A1	12/30/2004	Yongjun Jeff Hu			
	AH						

FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes
	AI	EP 0817251 A	1/1998	EPO			
	AJ						

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)		
AK		PCT/US2004/021156; Filed 6/30/2004; Search Report.
AL		PCT/US2004/021156; Filed 6/30/2004; Written Opinion Issued on 1/18/2005; 6 pps.
EXAMINER		DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-2308	SERIAL NO. 10/615,051
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT: Brian A. Vaartstra	
		FILING DATE 07/07/2003	GROUP 2823

U.S. PATENT DOCUMENTS							
*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						

FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	AF						
	AG						
	AH						

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
	AI		Chen et al., <i>Excimer Laser-Induced Ti Silicidation to Eliminate the Fine-Line Effect for Integrated Circuitry Device Fabrication</i> , 149 JOURNAL OF ELECTROCHEMICAL SOCIETY, No. 11, pp. G609-G612 (2002).
			Nishiyama et al., <i>Agglomeration Resistant Self-Aligned Silicide Process Using N₂ Implantation into TiSi₂</i> , 36 JPN. J. APPL. PHYS., Part 1, No. 6A, pp. 3639-3643 (June 1997).
	AJ		Wolf, Chapter 13: <i>Polycides and Salicides of TiSix, CoSi₂, and NiSi</i> , SILICON PROCESSING FOR THE VLSI ERA,
			Vol. IV, pp. 603-604 (pre-2003).
EXAMINER		DATE CONSIDERED	
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>			